Analog Power AMCC924NE

Dual N-Channel Logical Level MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low r_{DS(on)} and to ensure minimal power loss and heat con batt prir tele

ssipation. Typical applications are DC-DC			0.012 @ V _{GS}	= 45 V	9.2	1
nverters and power management in portable and	d	20	0.012 6 763	, – 1.5 1	<i></i>	
ttery-powered products such as computers,		20	$0.014 @ V_{GS}$	$_{\rm S} = 2.5 \rm{V}$	8.5	
inters, PCMCIA cards, cellular and cordless ephones.	(Py)		DFN 3x3 Top View	D	D	

 $V_{DS}(V)$

S2 🔲 3

G2 🔲 4

PRODUCT SUMMARY

 $r_{DS(on)}(OHM)$

□ D

□ D □ D

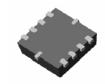
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- Low $r_{DS(on)}$ provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe HALOGEN DFN 3x3 saves board space
- Fast switching speed
- High performance trench technology



RoHS





MOSFET

N-Channel

MOSFET

 $I_{D}(A)$

ESD Protected 2000V

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)							
Parameter		Symbol	Maximum	Units			
Drain-Source Voltage	V_{DS}	20	V				
Gate-Source Voltage	V_{GS}	±8	V				
Continuous Drain Current ^a	$T_A=25^{\circ}C$	J.,	9.2				
Continuous Drain Current	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1D	7.5	A			
Pulsed Drain Current ^b	I_{DM}	±40					
Continuous Source Current (Diode Conduction) ^a		I_S	1.5	A			
D a	$T_A=25^{\circ}C$	D_	1.5	W			
Power Dissipation ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	Гр	1.0	۷V			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150	°C			

THERMAL RESISTANCE RATINGS								
Parameter		Symbol	Тур	Max				
Maximum Junction-to-Ambient ^a	t <= 10 sec	D	72	83	°C/W			
	Steady State	R_{thJA}	100	120				

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature b.

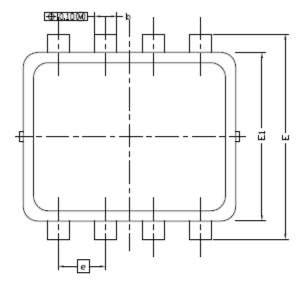
SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)								
Parameter	Symbol	Test Conditions				Unit		
1 ai ainetei	Symbol	rest conditions	Min Typ		Max	Cint		
Static								
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}$, $I_{D} = 250 \text{ uA}$	0.3			V		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			±10	μΑ		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1	Δ		
Zero Gate Voltage Drain Current	*DSS	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	μΑ		
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α		
Drain-Source On-Resistance ^A	$r_{\mathrm{DS(on)}}$	VGS = 4.5 V, ID = 2 A			0.012	Ω		
Drain-Source On-Acsistance	-DS(0II)	$V_{GS} = 2.5 \text{ V}, \text{ ID} = 2 \text{ A}$			0.014	32		
Forward Tranconductance ^A	g_{fs}	$V_{DS} = 10 \text{ V}, I_{D} = 2 \text{ A}$		25		S		
Diode Forward Voltage ^A	V_{SD}	$I_S = 2 A, V_{GS} = 0 V$		0.89		V		
Dynamic ^b								
Total Gate Charge	Q_{g}			13.4				
Gate-Source Charge	Q_{gs}	V_{DS} =10V, V_{GS} =4.5V, I_{D} =2A		0.9		nC		
Gate-Drain Charge	Q_{gd}			2.0				
Turn-On Delay Time	$t_{d(on)}$			18				
Rise Time	t _r	$V_{DD}=10V$, $V_{GS}=4.5V$, $I_{D}=1A$,		25		, C		
Turn-Off Delay Time	$t_{d(off)}$	$R_{\text{GEN}} = 10\Omega$		50		nS		
Fall-Time	t_{f}			25		<u> </u>		

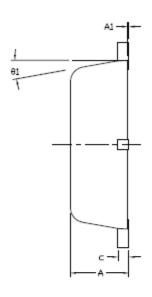
Notes

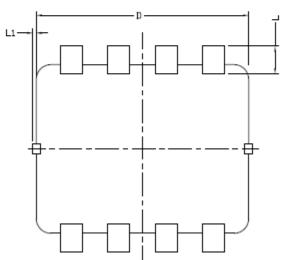
- a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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Package Information







DIM.	MIL	LIMETE	RS	INCHES			
DIM	MIN	M	MAX	MIN	M	MAX	
Α	0.700	0.80	0.900	0.0276	0.0315	0.0354	
A1	0.00		0.05	0.000 0		200.0	
О	0,24	0,30	0,35	0,009	0,012	0,014	
С	0.08	0.152	0.25	0.003	0.006	0.010	
D	2 90 BSC			0.114 BSC			
Ε	2.80 BSC 0.110 BSC						
E1	2.30 BSC 0.091 BSC						
6	0.65 BSC			0.059 B2C			
Г	0.20	0.375	0.450	0.008	0.0148	0.0177	
L1	0		0.100	0		0.004	
91	0*	10°	12*	0*	10*	12*	